Oleg Komkov

List of Publications by Year
in descending order

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46	288	933264	1058333
papers	citations	10 h-index	14 g-index

46	46	46	134
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Study of structural and optical properties of a dual-band material based on tin oxides and GeSiSn compounds. Applied Surface Science, 2022, 573, 151615.	3.1	2
2	Investigation of infrared photoluminescence spectra of Ge_{1-x-y}Si_xSn_y/Si nanostructures. Journal of Physics: Conference Series, 2022, 2227, 012009.	0.3	0
3	Tuning the structural and optical properties of GeSiSn/Si multiple quantum wells and GeSn nanostructures using annealing and a faceted surface as a substrate. Applied Surface Science, 2022, 593, 153421.	3.1	7
4	Epitaxial growth of peculiar GeSn and SiSn nanostructures using a Sn island array as a seed. Applied Surface Science, 2021, 553, 149572.	3.1	4
5	Effect of surface morphology on macroscale and microscale optical properties of layered InSe grown by molecular beam epitaxy. Journal of the Optical Society of America B: Optical Physics, 2021, 38, 2579.	0.9	1
6	Infrared Photoreflectance of IIIâ€“V Semiconductor Materials (Review). Physics of the Solid State, 2021, 63, 1181-1204.	0.2	1
7	Characterization of In(Ga,Al)As/GaAs metamorphic heterostructures for mid-IR emitters by FTIR photoreflectance spectroscopy. Journal of Physics: Conference Series, 2021, 2086, 012140.	0.3	0
8	Investigation of Built-in Electric Fields at the GaSe/GaAs Interface by Photoreflectance Spectroscopy. Semiconductors, 2020, 54, 1198-1204.	0.2	9
9	Molecular Beam Epitaxy of Layered Group III Metal Chalcogenides on GaAs(001) Substrates. Materials, 2020, 13, 3447.	1.3	16
10	Effect of the Crystallographic Orientation of GaSb Films on Their Structural Properties during MBE Heteroepitaxy on Vicinal Si(001) Substrates. Semiconductors, 2020, 54, 1548-1554.	0.2	2
11	Measurement of Infrared Photoluminescence Spectra by Gated Integration with Active Baseline Subtraction. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2020, 128, 131-136.	0.2	0
12	Effect of design and stress relaxation on structural, electronic, and luminescence properties of metamorphic InAs(Sb)/In(Ga,Al)As/GaAs mid-IR emitters with a superlattice waveguide. Journal of Applied Physics, 2020, 127, 125706.	1.1	4
13	Investigation of energy transitions in MoS2 by photoreflectance spectroscopy method. Journal of Physics: Conference Series, 2020, 1695, 012111.	0.3	0
14	Peculiarities of the energy spectrum of InSb/InAs/InGaAs/InAlAs/GaAs nanoheterostructures revealed by room temperature photomodulation FTIR spectroscopy. Japanese Journal of Applied Physics, 2019, 58, 050923.	0.8	4
15	Effect of Strongly Mismatched GaAs and InAs Inserts in a InAlAs Buffer Layer on the Structural and Optical Properties of Metamorphic InAs(Sb)/InGaAs/InAlAs/GaAs Quantum-Confined Heterostructures. JETP Letters, 2019, 109, 377-381.	0.4	4
16	Interpretation of photoluminescence spectra of metamorphic InAlAs/GaAs heterostructures. Journal of Physics: Conference Series, 2019, 1410, 012167.	0.3	0
17	Infrared photoluminescence spectra measurements using boxcar integrator in the active baseline subtraction mode. Journal of Physics: Conference Series, 2019, 1400, 066035.	0.3	2
18	Metamorphic InAs(Sb)/InGaAs/InAlAs nanoheterostructures grown on GaAs for efficient mid-IR emitters. Progress in Crystal Growth and Characterization of Materials, 2019, 65, 20-35.	1.8	17

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19	Infrared photoreflectance of InSb-based two-dimensional nanostructures. Journal of the Optical Society of America B: Optical Physics, 2019, 36, 910.	0.9	8
20	Contactless Measurement of Electron Concentration in Undoped Homoepitaxial InSb Layers. Journal of Communications Technology and Electronics, 2018, 63, 289-291.	0.2	2
21	Radiative versus non-radiative recombination in high-efficiency mid-IR InSb/InAs/In(Ga,Al)As/GaAs metamorphic nanoheterostructures. Journal Physics D: Applied Physics, 2018, 51, 055106.	1.3	10
22	Investigation of GaAs/AlGaAs superlattice by photoreflectance method. Journal of Physics: Conference Series, 2018, 1038, 012124.	0.3	4
23	InSb/InAs/InGa(Al)As/GaAs(0 0 1) metamorphic nanoheterostructures grown by MBE and emitting beyond 3 Î¼m. Journal of Crystal Growth, 2017, 477, 97-99.	0.7	14
24	Contactless characterization of manganese and carbon delta-layers in gallium arsenide. Semiconductors, 2017, 51, 1420-1426.	0.2	2
25	FTIR photoreflectance of narrow-gap heterostructures based on AlxIn1-xSb alloys. Journal of Physics: Conference Series, 2017, 917, 062025.	0.3	2
26	Enhanced room-temperature 3.5 Âµm photoluminescence in stress-balanced metamorphic In(Sb,As)/In(Ga,Al)As/GaAs quantum wells. Applied Physics Express, 2017, 10, 121201.	1.1	13
27	Temperature-dependent photoluminescence of InSb/InAs nanostructures with InSb thickness in the above-monolayer range. Journal Physics D: Applied Physics, 2016, 49, 285108.	1.3	21
28	Evaluation of nitrogen incorporation into bulk 4H-SiC grown on seeds of different orientation from optical absorption spectra. Journal of Physics: Conference Series, 2016, 741, 012043.	0.3	8
29	Photoreflectance of indium antimonide. Physics of the Solid State, 2016, 58, 2394-2400.	0.2	13
30	Metamorphic InAs/InGaAs/InAlAs quantum wells with submonolayer InSb insertions emitted in the mid-infrared spectral range. Technical Physics Letters, 2016, 42, 1038-1040.	0.2	9
31	Phase-sensitive photoreflectance investigation of InGaAs/GaAs quantum well structures. , 2016, , .		0
32	Photoluminescence of undoped InAs autoepitaxial layers. Journal of Physics: Conference Series, 2015, 643, 012051.	0.3	0
33	Determination of the indium arsenide autoepitaxial layersâ€™ thickness by Fourier-Transform Infrared Spectroscopy. Russian Microelectronics, 2015, 44, 575-578.	0.1	2
34	Determination of InSb/AlInSb quantum well energy spectrum. Journal of Physics: Conference Series, 2014, 541, 012085.	0.3	5
35	Photoreflectance of GaAs structures with a Mn Î´-doped layer. Technical Physics Letters, 2013, 39, 1008-1011.	0.2	5
36	Photomodulation fourier transform infrared spectroscopy of semiconductor structures: Features of phase correction and application of method. Technical Physics Letters, 2013, 39, 1071-1073.	0.2	21

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37	Determination of the thickness and spectral dependence of the refractive index of Al x In1 âˆ' x Sb epitaxial layers from reflectance spectra. Semiconductors, 2013, 47, 292-297.	0.2	9
38	Photoreflectance characterization of gallium arsenide. Russian Microelectronics, 2012, 41, 508-510.	0.1	7
39	Molecular Beam Epitaxy Growth and Optical Characterization of Al[sub x]In[sub 1-x]Sbâ•GaAs Heterostructures. , 2011, , .		5
40	Optical Properties of Epitaxial Al x In1âˆ'x Sb Alloy Layers. Semiconductors, 2011, 45, 1425-1429.	0.2	10
41	10.1007/s11455-008-1011-0. , 2010, 34, 37.		0
42	Excitonic effects and Franz-Keldysh oscillations in photoreflectance of ultrapure GaAs epilayers. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 842-846.	0.8	9
43	Determination of the free carrier concentration in ultra-pure GaAs epilayers by a photoreflectance technique. Technical Physics Letters, 2008, 34, 37-39.	0.2	13
44	Effect of external electric field on the probability of optical transitions in InGaAs/GaAs quantum wells. Semiconductors, 2006, 40, 592-597.	0.2	17
45	Effect of electric field on the probability of optical transitions in InGaAs/GaAs quantum wells observed by photo- and electroreflectance methods. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 1270-1274.	0.8	6
46	Structural and Optical Properties of a Hybrid Material Based on Tin Oxides and Multilayer Periodic Structures with Pseudomorphic GeSiSn Layers. Russian Physics Journal, 0, , 1.	0.2	0